

rfmd.com

XD010-22S-D2F(Y)

1805 MHz to 1880 MHz CLASS A/AB 12 W POWER AMPLIFIER MODULE

RFMD Green, RoHS Compliant, Pb-Free (Y Part Number)
Package: D



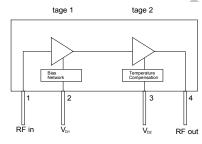
Product Description

RFMD's XD010-22S-D2F 12W power module is a robust 2-Stage Class A/AB amplifier module for use in the driver stages of GSM/EDGE RF power amplifiers for cellular base stations. The power transistors are fabricated using RFMD's latest, high performance LDMOS process. This unit operates from a single volage and has internal temperature compensation of the bias voltage to ensure stable performance over the full temperature range. It is a drop-in, no-tune solution for medium power applications requiring high efficiency, excellent linearity, and unit-to-unit repeatability. It

is internally matched to 50Ω .



Functional Block Diagram



Case Flange = Ground

Features

- Available in RoHS Compliant Packaging
- 50Ω RF Impedance
- 12W output P_{1dB}
- Single Supply Operation: Nominally 28V
- High Gain: 31dB at 1840MHz
- High Efficiency: 25% at 1840MHz
- Advanced, XeMOS II LDMOS FETS

Applications

- Base Station PA Driver
- Repeater
- GSM/EDGE

| Parameter | | Specification | | Unit | Condition |
|--|------|---------------|------|-------|-----------------------------|
| raiailletei | Min. | Тур. | Max. | UIIIL | Condition |
| Frequency of Operation | 1805 | | 1880 | MHz | |
| Output Power at 1dB Compression (Single Tone) | 10 | 12 | | W | |
| Gain | 28.5 | 31 | | dB | 5W Output Power (CW) |
| Peak to Peak Gain Variation | | 0.5 | 1.0 | dB | |
| Drain Efficiency | 20 | 25 | | % | 10W CW |
| Input Return Loss | 10 | 14 | | dB | 5W Output (CW) |
| RMS EVM | | 1.5 | | % | 5W EDGE output |
| Peak EVM | | 5 | | % | 5W EDGE output |
| Third Order IMD | -26 | -32 | | dBc | 10W PEP (Two Tone; 1MHz ΔF) |
| Deviation from Linear Phase (Peak to Peak) | | 0.5 | | Deg | |
| Thermal Resistance Stage 1 (Junction to Case) | | 11 | | °C/W | |
| Thermal Resistance Stage 2 (Junction to Case) | | 4 | | °C/W | |

Test Conditions: $Z_{IN} = Z_{OUT} = 50\Omega$ $V_{DD} = 28.0V$ $I_{DQ1} = 230 \text{ mA}$ $I_{DQ2} = 115 \text{ mA}$ $T_{FLANGE} = 25 ^{\circ}\text{C}$



Absolute Maximum Ratings

| Parameter | Rating | Unit |
|---|---------------------|-------|
| 1 st Stage Bias Voltage (V _{D1}) | 35 | V |
| 2 nd Stage Bias Voltage (V _{D2}) | 35 | V |
| RF Input Power | +20 | dBm |
| Load Impedance for Continuous Operation Without Damage | 5:1 | VSWR |
| Output Device Channel Temperature | +200 | °C |
| Operating Temperature Range | -20 to +90 | °C |
| Storage Temperature Range | -40 to +100 | °C |
| ESD Rating - Human Body Model, JEDEC Document - JESD22-A114-B | 8000 | V |
| MTTF - 85°C Leadframe, 200°C Channel | 1.2×10 ⁶ | Hours |

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.



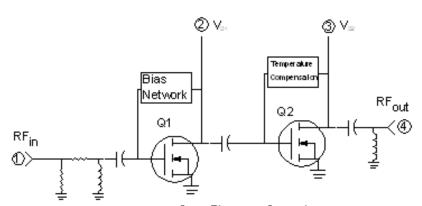
Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective 2002/95/EC (at time of this document revision).

The information in this publication is believed to be accurate and reliable. However, no responsibility is assumed by RF Micro Devices, Inc. ("RFMD") for its use, nor for any infringement of patents, or other rights of third parties, resulting from its use. No license is granted by implication or otherwise under any patent or patent rights of RFMD. RFMD reserves the right to change component circuity, recommended application circuity and specifications at any time without prior notice.

Simplified Device Schematic

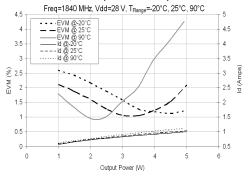




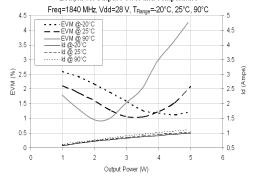


Typical Performance Curves

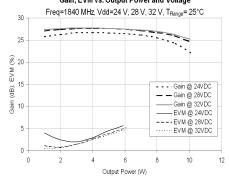




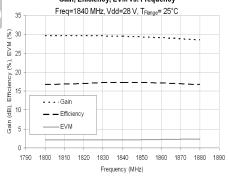
EVM, Id vs. Output Power and Temperature



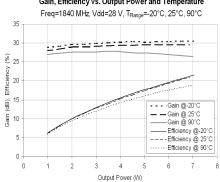
Gain, EVM vs. Output Power and Voltage



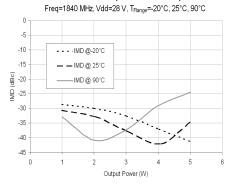
Gain, Efficiency, EVM vs. Frequency



Gain, Efficiency vs. Output Power and Temperature



Two Tone IMD vs. Output Power and Temperature





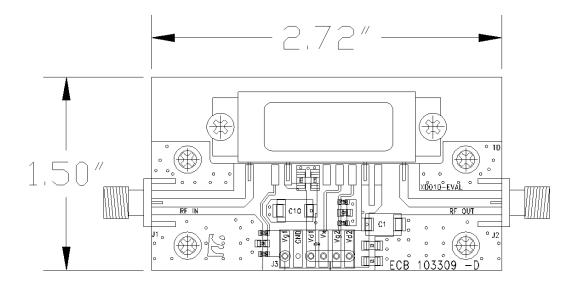
| Pin | Function | Description |
|--------|----------|--|
| 1 | RFIN | Module RF input. This pin is internally connected to DC ground. Do not apply DC voltages to the RF leads. Care must be taken to protect against video transients that may damage the active devices. |
| 2 | VD1 | This is the drain voltage for the first stage. Nominally +28Vdc |
| 3 | VD2 | This is the drain voltage for the 2 nd stage of the amplifier module. The 2 nd stage gate bias is temperature compensated to maintain constant quiescent drain current over the operating temperature range. See Note 1. |
| 4 | RFOUT | Module RF output. This pin is internally connected to DC ground. Do not apply DC voltages to the RF leads. Care must be taken to protect against video transients that may damage the active devices. |
| Flange | GND | Exposed area on the bottom side of the package needs to be mechanically attached to the ground plane of the board for optimum thermal and RF performance. See mounting instructions in application note AN-060 on RFMD's web site. |

Note 1: The internally generated gate voltage is thermally compensated to maintain constant quiescent current over the temperature range listed in the data sheet. No compensation is provided for gain changes with temperature. This can only be accomplished with AGC external to the module.

Note 2: Internal RF decoupling is included on all bias leads. No additional bypass elements are required, however some applications may require energy storage on the drain leads to accommodate time-varying waveforms.

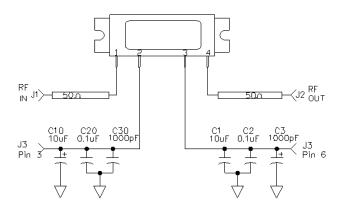
Note 3: This module was designed to have its leads hand soldered to an adjacent PCB. The maximum soldering iron tip temperature should not exceed 700° F, and the soldering iron tip should not be in direct contact with the lead for longer than 10 seconds. Refer to app note AN060 (www.RFMD.com) for further installation instructions.

Test Board Layout





Test Board Schematic with module connections shown



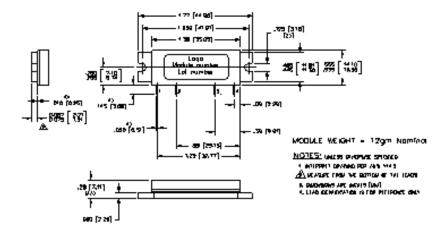
Test Board Bill of Materials

| Component | Description | Manufacturer | | |
|-----------------|---|--------------|--|--|
| PCB | Rogers 4350, ε_r =3.5, Thickness=30mils | Rogers | | |
| J1, J2 | SMA, RF, Panel Mount Tab W / Flange | Johnson | | |
| J3 | MTA Post Header, 6 Pin, Rectangle, Polarized, Surface Mount | AMP | | |
| C1, C10 | Cap, 10 F, 35V, 10%, Tant, Elect, D | Kemet | | |
| C2, C20 | Cap, 0.1μF, 100V, 10%, 1206 | Johanson | | |
| C3, C30 | Cap, 1000pF, 100V, 10%, 1206 | Johanson | | |
| C25, C26 | Cap, 68pF, 250V, 5%, 0603 | ATC | | |
| C21, C22 | Cap, 0.1mF, 100V, 10%, 0805 | Panasonic | | |
| C23, C24 | Cap, 1000pF, 100V, 10%, 0603 | AVX | | |
| Mounting Screws | 4-40 X 0.250" | Various | | |



Package Outline Drawing

Dimensions in inches (millimeters)
Refer to drawing posted at www.rfmd.com for tolerances.



Recommended PCB Cutout and Landing Pads for the D4F Package

Dimensions in inches (millimeters)

